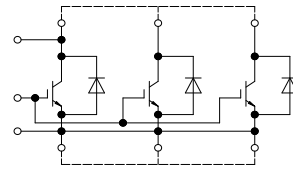


IHM-B 模块 采用第三代高速沟槽栅/场终止IGBT和第三代发射极控制二极管
 IHM-B module with fast Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode



external connection
(to be done)

$V_{CES} = 3300V$
 $I_{C\ nom} = 1500A / I_{CRM} = 3000A$

潜在应用

- UPS系统
- 中压变流器
- 斩波应用
- 牵引变流器
- 电机传动
- 风力发电机

Potential Applications

- UPS systems
- Medium voltage converters
- Chopper applications
- Traction drives
- Motor drives
- Wind turbines

电气特性

- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} 带正温度系数
- 低 V_{CEsat}
- 低开关损耗
- 无与伦比的坚固性
- 高直流电压稳定性
- 高短路能力

Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- V_{CEsat} with positive temperature coefficient
- Low V_{CEsat}
- Low switching losses
- Unbeatable robustness
- High DC stability
- High short-circuit capability

机械特性

- IHM B 封装
- 封装的 CTI > 600
- 碳化硅铝 (AlSiC) 基板提供更高的温度循环能力
- 绝缘的基板

Mechanical Features

- IHM B housing
- Package with CTI > 600
- AlSiC base plate for increased thermal cycling capability
- Isolated base plate

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_{CES}	3300 3300	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	I_{CDC}	1500	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	3000	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1500\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	2,55 3,00 3,15	3,10 3,45	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 72,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 1800\text{ V}$		Q_G	42,0			μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,42			Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	280			nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	6,00			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 3300\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,0\ \Omega, C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,60 0,60 0,60			μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,0\ \Omega, C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,55 0,55 0,55			μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,5\ \Omega, C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	3,00 3,20 3,20			μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,5\ \Omega, C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,30 0,35 0,35			μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}, L_{\sigma} = 85\text{ nH}$ $di/dt = 4500\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 0,47\ \Omega$ $C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1900 2550 2900			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1500\text{ A}, V_{CE} = 1800\text{ V}, L_{\sigma} = 85\text{ nH}$ $du/dt = 2100\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 1,5\ \Omega$ $C_{GE} = 330\text{ nF}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1600 2100 2300			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 2500\text{ V}$ $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{sc}	6400			A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}			7,35	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}			10,0	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = -40^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_{RRM}	3300 3300	V
连续正向直流电流 Continuous DC forward current		I_F	1500	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	3000	A
I^2t -值 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	590 550	kA^2s kA^2s
最大损耗功率 Maximum power dissipation	$T_{vj} = 150^{\circ}\text{C}$	P_{RQM}	2400	kW
最小开通时间 Minimum turn-on time		$t_{on\ min}$	10,0	μs

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1500\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1500\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 1500\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	3,10 2,75 2,65	3,85 3,25	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1500\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	1500 1800 1850		A A A
恢复电荷 Recovered charge	$I_F = 1500\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	650 1350 1600		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1500\text{ A}, -di_F/dt = 4500\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 1800\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	650 1650 1950		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		13,0	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	11,0		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40	150	$^{\circ}\text{C}$

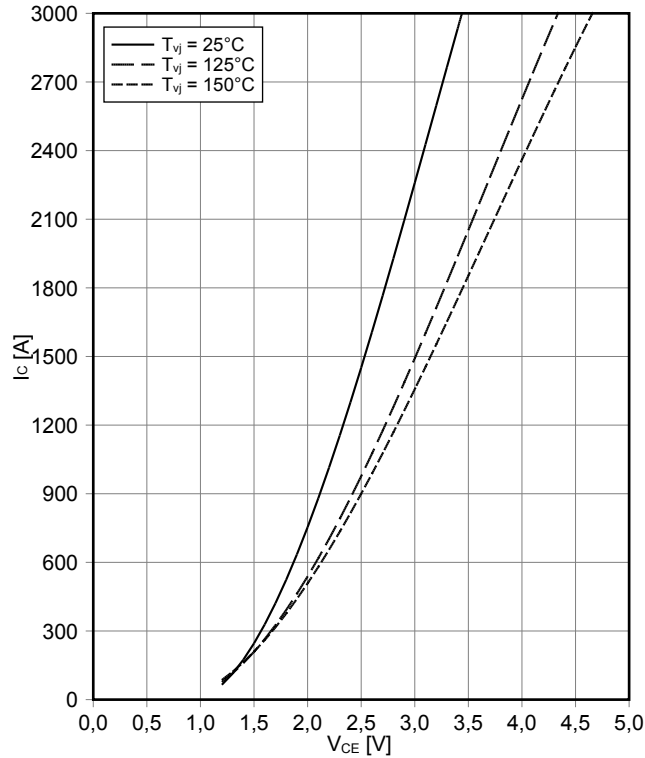
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	6,0		kV
局部放电停止电压 Partial discharge extinction voltage	RMS, f = 50 Hz, Q _{PD} ≤ 10 pC	V _{ISOL}	2,6		kV
DC 稳定性 DC stability	T _{vj} = 25°C, 100 fit	V _{CE D}	2100		V
模块基板材料 Material of module baseplate			AISiC		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		32,2		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,1		mm
相对电痕指数 Comperative tracking index		CTI	> 600		
min. typ. max.					
杂散电感, 模块 Stray inductance module		L _{sCE}	6,0		nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC+EE'}	0,12		mΩ
储存温度 Storage temperature		T _{stg}	-40	150	°C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25	5,75	Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,8 8,0	- 10	2,1 Nm Nm
重量 Weight		G	1200		g

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

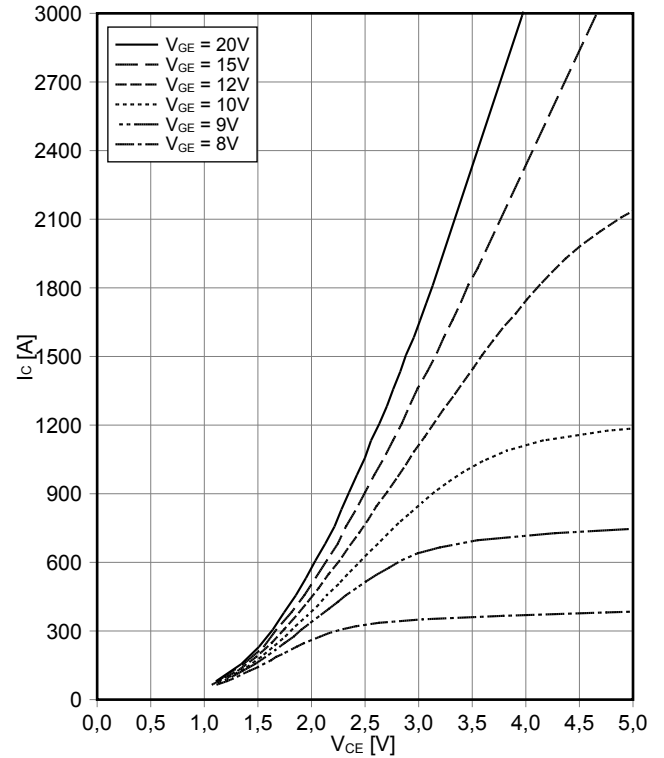
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

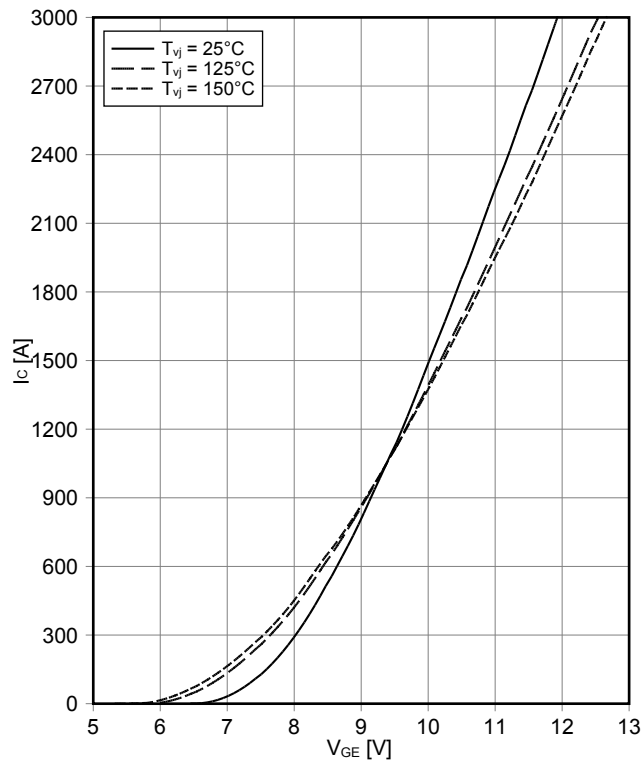
$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

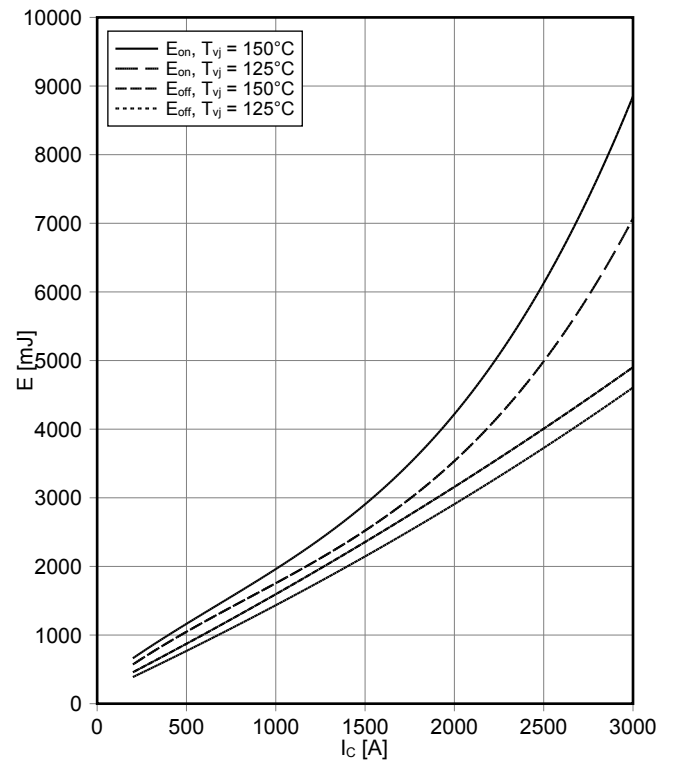
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.47\ \Omega$, $R_{Goff} = 1.5\ \Omega$, $V_{CE} = 1800\text{ V}$, $C_{GE} = 330\text{ nF}$

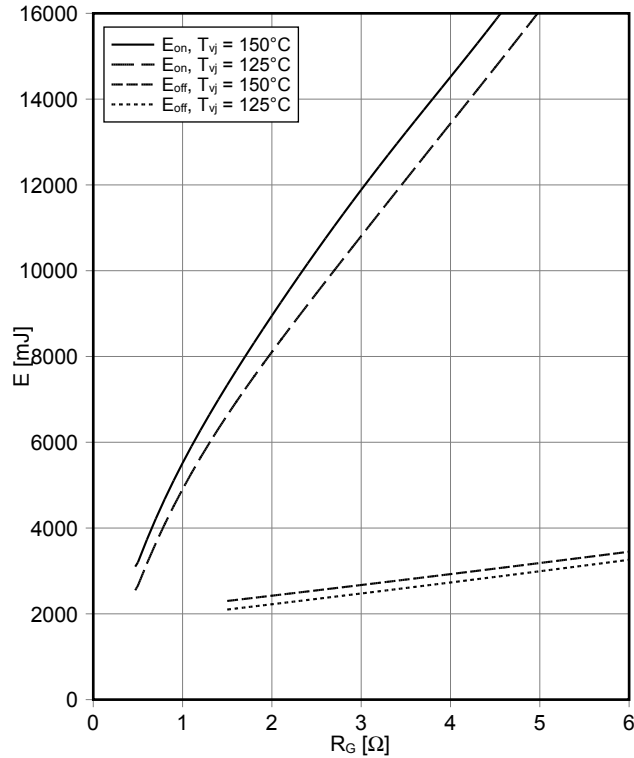


开关损耗 IGBT, 逆变器 (典型)

switching losses IGBT, Inverter (typical)

$$E_{on} = f(R_G), E_{off} = f(R_G)$$

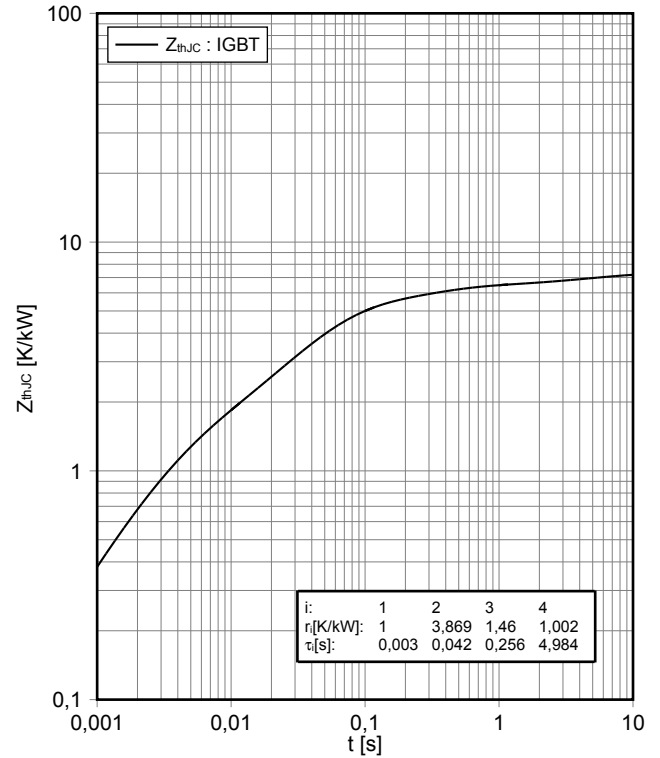
$$V_{GE} = \pm 15 \text{ V}, I_C = 1500 \text{ A}, V_{CE} = 1800 \text{ V}, C_{GE} = 330 \text{ nF}$$



瞬态热阻抗 IGBT, 逆变器

transient thermal impedance IGBT, Inverter

$$Z_{thJC} = f(t)$$

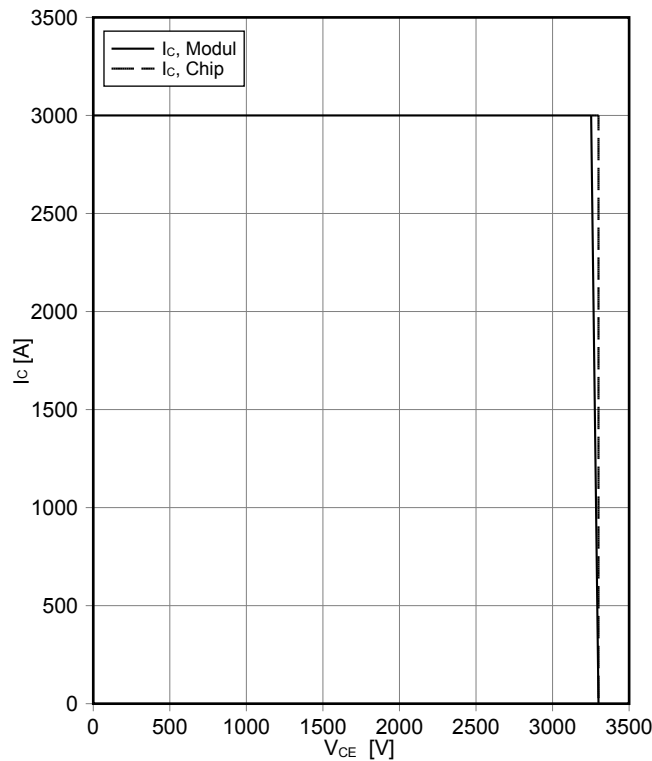


反偏安全工作区 IGBT, 逆变器 (RBSOA)

reverse bias safe operating area IGBT, Inverter (RBSOA)

$$I_C = f(V_{CE})$$

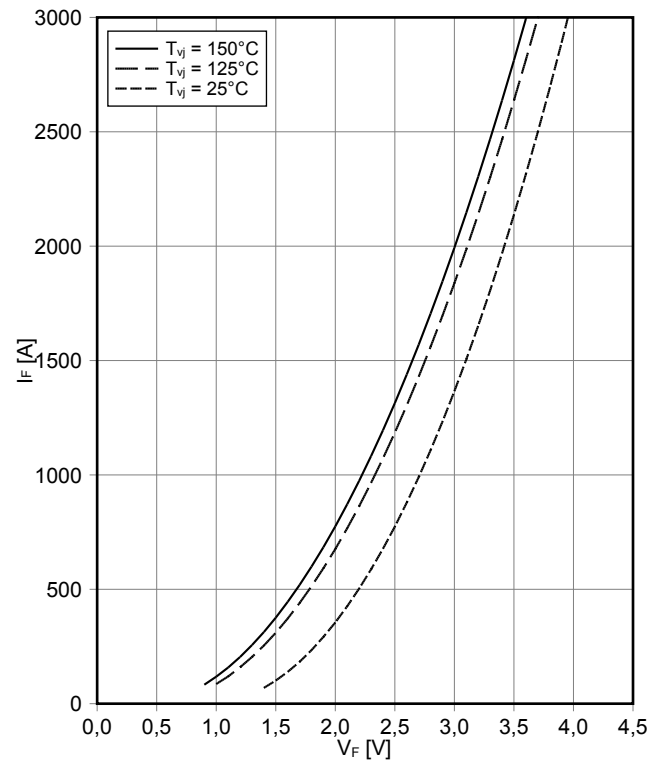
$$V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.5 \text{ } \Omega, T_{vj} = 150^\circ\text{C}, C_{GE} = 330 \text{ nF}$$



正向偏压特性 二极管, 逆变器 (典型)

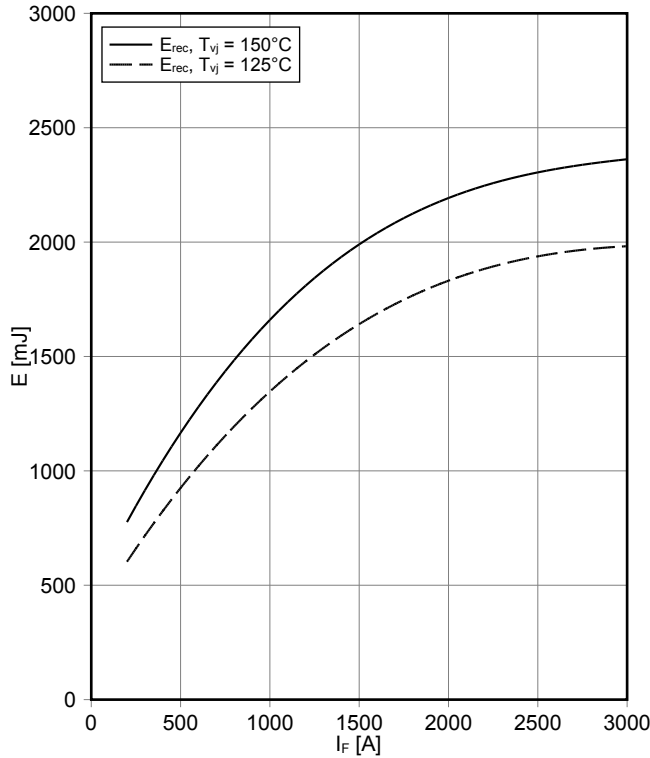
forward characteristic of Diode, Inverter (typical)

$$I_F = f(V_F)$$



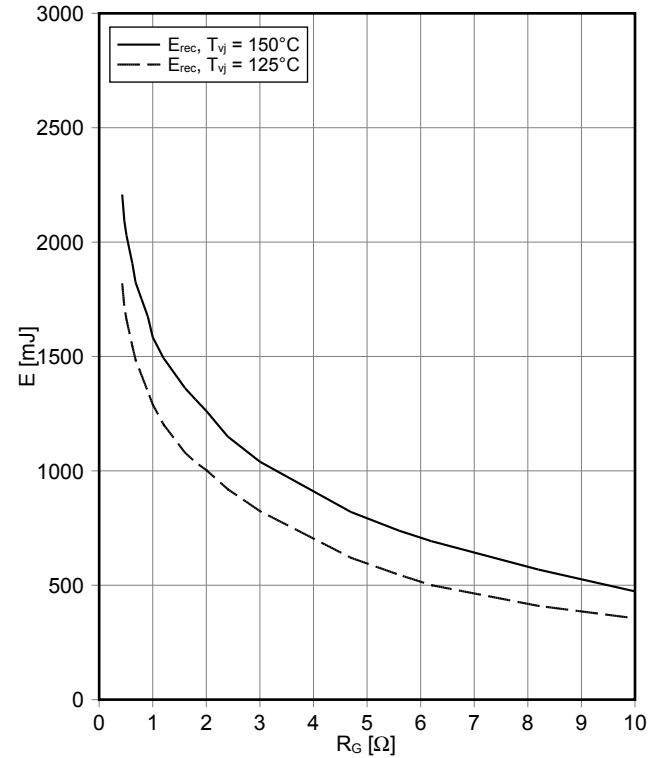
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 0.47 \Omega, V_{CE} = 1800 V$



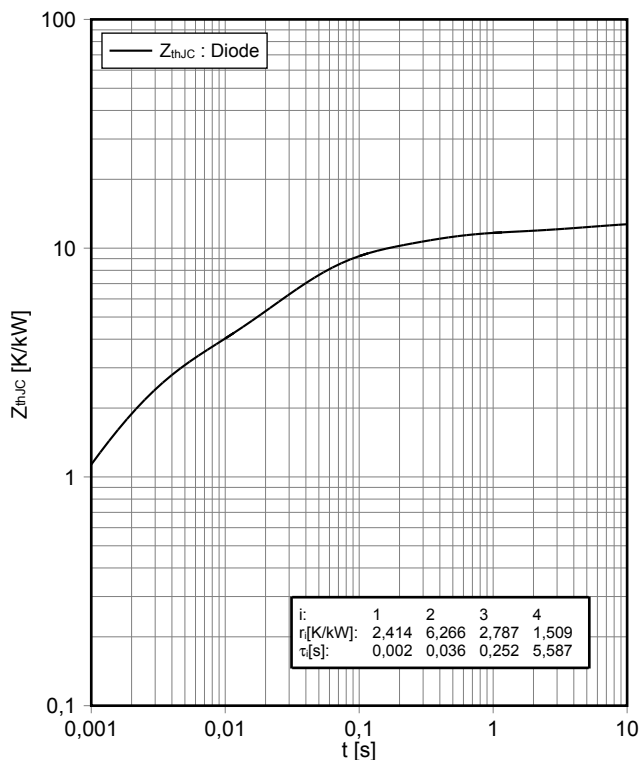
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 1500 A, V_{CE} = 1800 V$



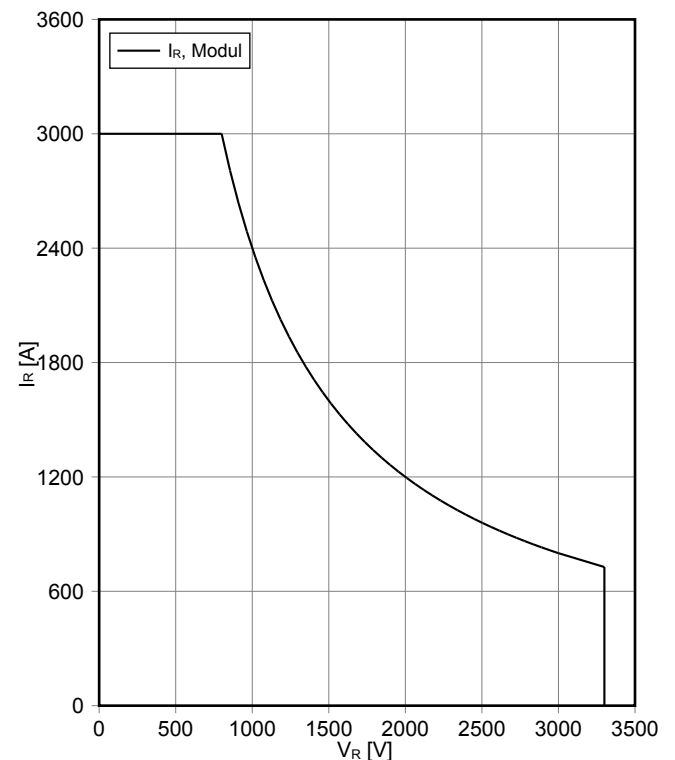
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

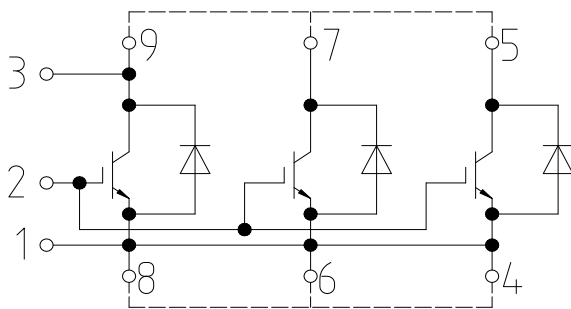


安全工作区 二极管,逆变器 (SOA)
safe operation area Diode, Inverter (SOA)

$I_R = f(V_R)$
 $T_{vj} = 150^\circ C$

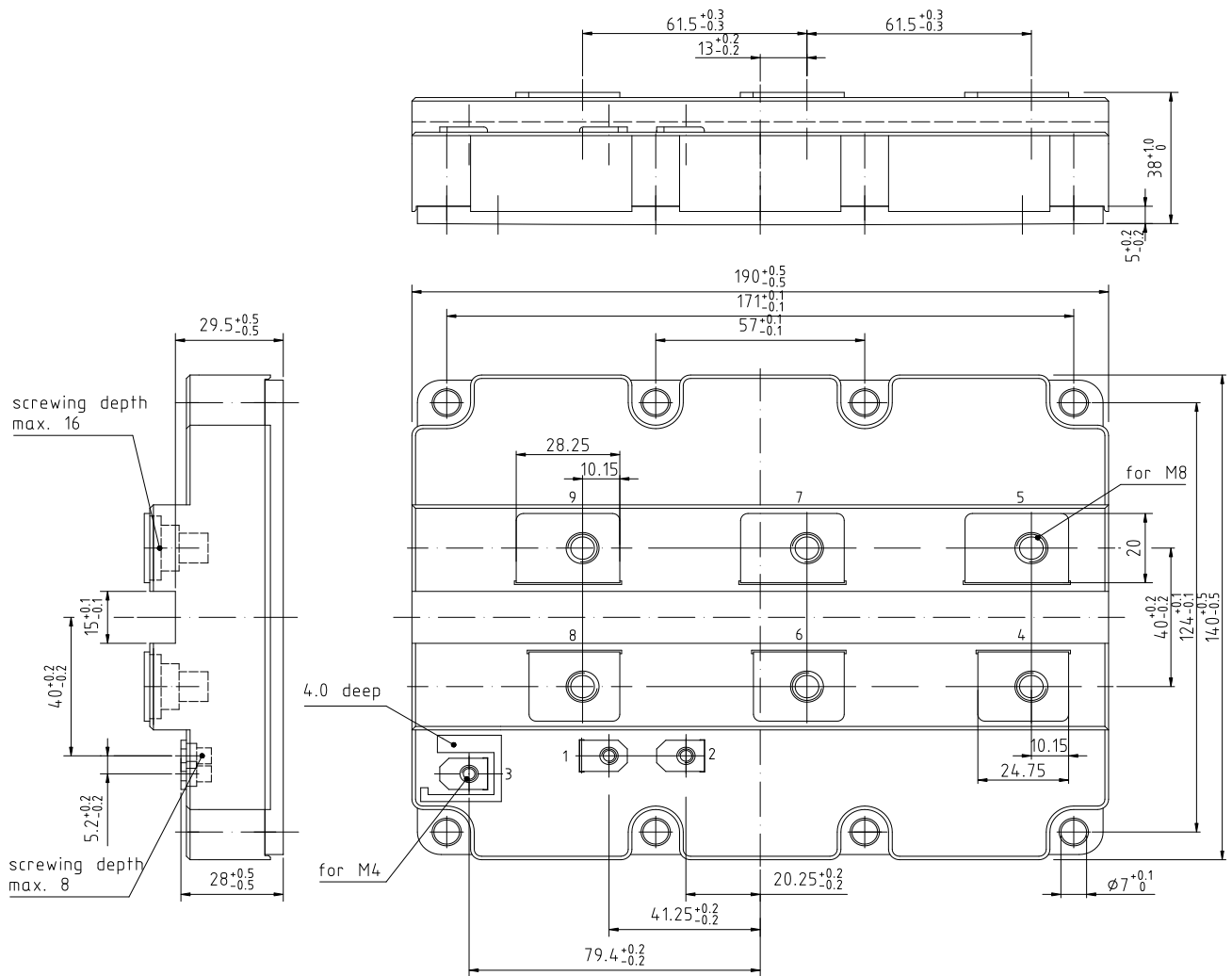


接线图 / Circuit diagram



external connection
(to be done)

封装尺寸 / Package outlines



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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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